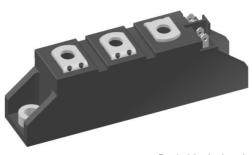
Thyristor Module

MCC19-12io1B

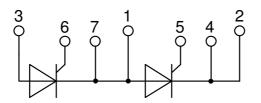
V_{RRM}	<i>=</i> 2x 1200 V		
I _{tav}	=	18 A	
Vτ	=	1.57 V	

Phase leg

Part number MCC19-12io1B



Backside: isolated **E**72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

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Data according to IEC 60747and per semiconductor unless otherwise specified

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MCC19-12io1B

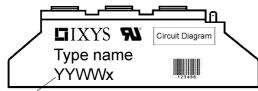
Thyristo				1	Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Uni
V _{RSM/DSM}	max. non-repetitive reverse/forwa	rd blocking voltage	$T_{vJ} = 25^{\circ}C$			1300	\ \
V _{RRM/DRM}	max. repetitive reverse/forward bl		$T_{VJ} = 25^{\circ}C$			1200	١
R/D	reverse current, drain current	V _{R/D} = 1200 V	$T_{vJ} = 25^{\circ}C$			100	μ/
		V _{R/D} = 1200 V	$T_{vJ} = 125^{\circ}C$			3	m/
V _T	forward voltage drop	$I_{T} = 40 \text{ A}$	$T_{vJ} = 25^{\circ}C$			1.56	١
		I _T = 80 A				2.05	١
		$I_{T} = 40 \text{ A}$	$T_{vJ} = 125 \degree C$			1.57	١
		I _T = 80 A				2.29	١
ITAV	average forward current	$T_c = 85^{\circ}C$	$T_{vJ} = 125^{\circ}C$			18	ŀ
I _{T(RMS)}	RMS forward current	180° sine				28	ļ
V _{T0}	threshold voltage		T _{vJ} = 125°C			0.85	١
r _T	slope resistance } for power lo	oss calculation only				18	m۵
R _{thJC}	thermal resistance junction to cas	e				1.3	K/W
R _{thCH}	thermal resistance case to heatsi				0.20		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			77	N
I _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{v.i} = 45^{\circ}C$			400	ļ
1.51	-	t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			430	ļ
		t = 10 ms; (50 Hz), sine	T _{v.I} = 125°C			340	ļ
		t = 8,3 ms; (60 Hz), sine	$V_{\rm R} = 0 V$			365	
l²t	value for fusing	t = 0,0 ms; (50 Hz), sine	$T_{\rm V,I} = 45^{\circ}\rm C$			800	A ² s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			770	A ²
		t = 0,5 ms; (50 Hz), sine t = 10 ms; (50 Hz), sine	$T_{y_{J}} = 125^{\circ}C$			580	A ² s
		t = 8,3 ms; (60 Hz), sine	$V_{\rm NJ} = 123$ C $V_{\rm R} = 0$ V			555	A ² s
<u> </u>	junction capacitance	$V_{\rm B} = 400 \text{V}$ f = 1 MHz	$\frac{v_{R}}{T_{VJ}} = 25^{\circ}C$		22	555	pF
C,			$T_{vJ} = 25 \text{ C}$ $T_{c} = 125 \text{ °C}$		22	10	pr W
P _{GM}	max. gate power dissipation	$t_p = 30 \ \mu s$	$1_{\rm C} = 125 \rm C$			10	
-		t _P = 300 μs				5	M N
P _{GAV}	average gate power dissipation					0.5	N
(di/dt) _{cr}	critical rate of rise of current	$T_{vJ} = 125 ^{\circ}C; f = 50 \text{Hz}$ re	•			150	A/μ
		$t_{P} = 200 \mu s; di_{G}/dt = 0.45 A/\mu s; -$					
			on-repet., $I_{T} = 18 \text{ A}$				A/μ
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{vJ} = 125^{\circ}C$			1000	V/μ
		$R_{GK} = \infty$; method 1 (linear volta					1 1 1 1
V _{GT}	gate trigger voltage	$V_{\rm D} = 6 V$	$T_{vJ} = 25^{\circ}C$			1.5	١
			$T_{vJ} = -40 ^{\circ}\text{C}$			1.6	١
I _{GT}	gate trigger current	$V_{D} = 6 V$	$T_{vJ} = 25^{\circ}C$			100	mA
			$T_{vJ} = -40 ^{\circ}C$			200	mÆ
V _{gd}	gate non-trigger voltage	$V_{D} = \frac{2}{3} V_{DRM}$	$T_{vJ} = 125^{\circ}C$			0.2	١
	gate non-trigger current					5	m/
I.	latching current	t _p = 10 μs	$T_{v_J} = 25 \degree C$			450	m/
		$I_{G} = 0.45 \text{ A}; \ di_{G}/dt = 0.45 \text{ A}/\mu s$	3				
I _H	holding current	V _D = 6 V R _{GK} = ∞	$T_{vJ} = 25 ^{\circ}C$			200	m/
t _{gd}	gate controlled delay time	$V_{\rm D} = \frac{1}{2} V_{\rm DRM}$	$T_{VJ} = 25 ^{\circ}\text{C}$			2	μ
J-	-	$I_{\rm G} = 0.45 \text{A}; \text{di}_{\rm G}/\text{dt} = 0.45 \text{A}/\mu\text{s}$					
t _q	turn-off time	$V_{\rm R} = 100 \text{ V}; \ \text{I}_{\rm T} = 20 \text{ A}; \text{ V} = \frac{3}{2}$			150		μ
-4		$di/dt = 10 \text{ A}/\mu \text{s} dv/dt = 20 \text{ V}$					٣

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MCC19-12io1B

Package TO-240AA				Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					200	Α
T _{vj}	virtual junction temperature				-40		125	°C
T _{op}	operation temperature				-40		100	°C
T _{stg}	storage temperature				-40		125	°C
Weight						81		g
M _D	mounting torque				2.5		4	Nm
M _T	terminal torque				2.5		4	Nm
d _{Spp/App}	creenage distance on surfac	e striking distance through air	terminal to terminal	13.0	9.7			mm
d _{Spb/Apb}	creepage distance on surrac	e suiking ustance through an	terminal to backside	16.0	16.0			mm
V	isolation voltage	t = 1 second			3600			V
	t = 1 minute		50/60 Hz, RMS; lıso∟ ≤ 1 mA		3000			V



Date Code

ſ	Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
	Standard	MCC19-12io1B	MCC19-12io1B	Box	36	452831

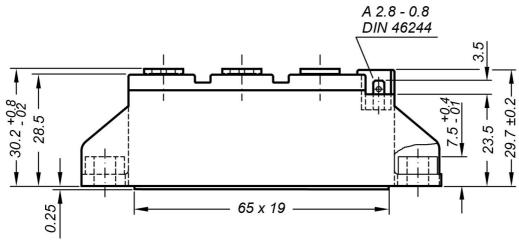
Similar Part	Package	Voltage class
MCMA25P1200TA	TO-240AA-1B	1200
MCMA35P1200TA	TO-240AA-1B	1200

Equiva	lent Circuits for	Simulation	* on die level	T _{vj} = 125 °C
	R ₀	Thyristor		
$V_{0 \text{ max}}$	threshold voltage	0.85		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	16.8		mΩ

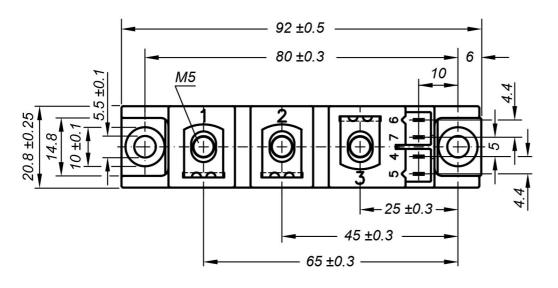
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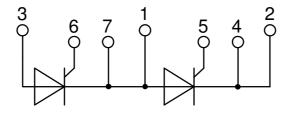
Outlines TO-240AA



General tolerance: DIN ISO 2768 class "c"



Optional accessories: Keyed gate/cathode twin plugs Wire length: 350 mm, gate = white, cathode = red UL 758, style 3751 Type **ZY 200L** (L = Left for pin pair 4/5) Type **ZY 200R** (R = Right for pin pair 6/7)



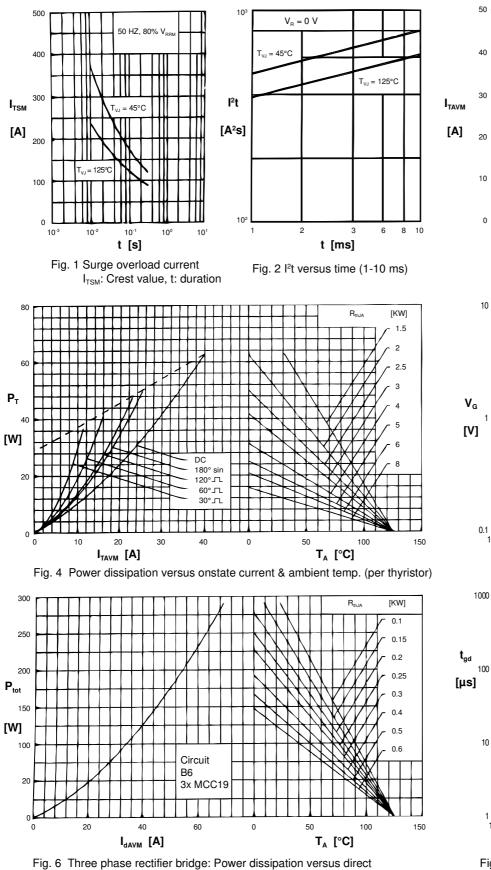
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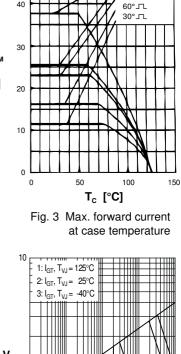
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DC

180° sin 120°-7⊓

Thyristor





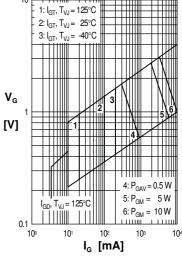


Fig. 5 Gate trigger charact.

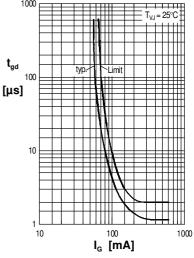


Fig. 7 Gate trigger delay time

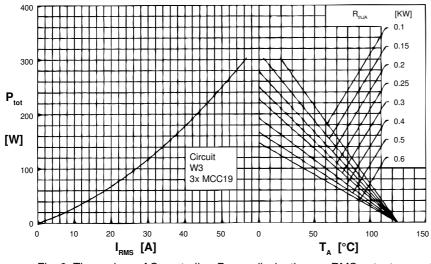
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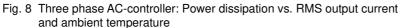


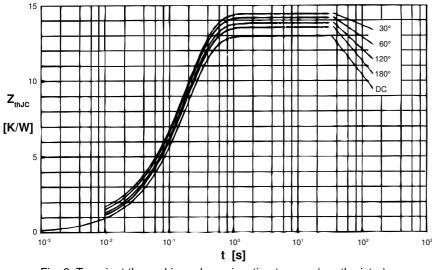
output current and ambient temperature

MCC19-12io1B

Thyristor

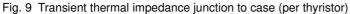


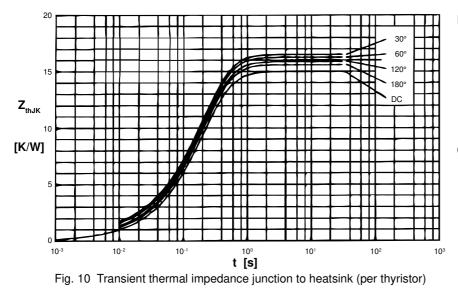




R_{thJ}	_o for va	arious c	onduct	tion angles d:
	d	R _{thJC} [k	(/W]	
	DC	1.30)	
	180°	1.3	5	
	120°	1.39	Э	
	60°	1.42	2	
	30°	1.4	5	
Cor	nstants	for Z _{th}	_c calcu	lation:
i	R _{thi} [K/	/W]	t _i [s]	
1	0.01	8 (0.0033	
2	0.04	1 ().0216	

0.1910





 $R_{_{thJK}}$ for various conduction angles d: d R_{thJK} [K/W] DC 1.50 180° 1.55 120° 1.59 60° 1.62 30° 1.65 Constants for $\boldsymbol{Z}_{_{thJK}}$ calculation: i R_{thi} [K/W] t_i [s] 1 0.018 0.0033 0.0216 0.041 2 3 0.1910 1.241

0.4600

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0.200

3

1.241